



T_c =25

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	12	V
Continuous Drain Current	I _{D@TC=25}	40	A
	I _{D@TC=75}	30.4	A
	I _{D@TC=100}	25.2	A
Pulsed Drain Current	I _{DM}	120	A
Total Power Dissipation	P _{D@TC=25}	46	W
Total Power Dissipation	P _{D@TA=25}	2.3	W
Operating Junction Temperature	T _J	-55 to 150	
Storage Temperature	T _{STG}	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	E _{AS}	180	mJ

Fig.1 Gate-Charge Characteristics

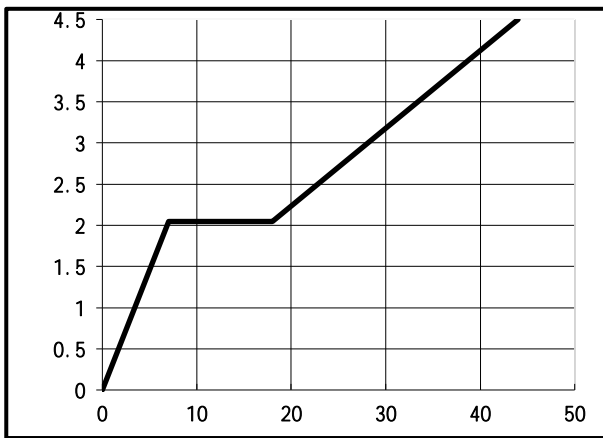


Fig.2 Capacitance Characteristics

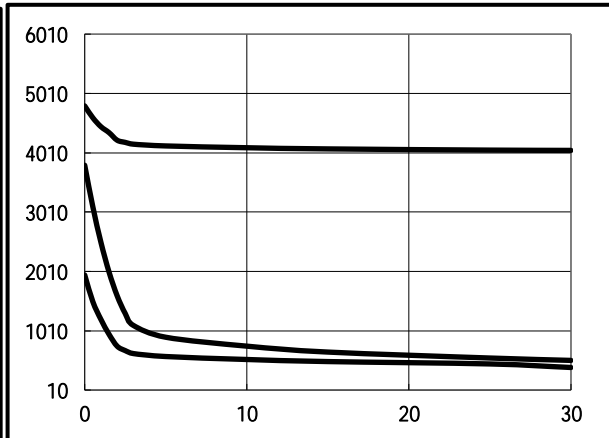


Fig.2 Power Dissipation

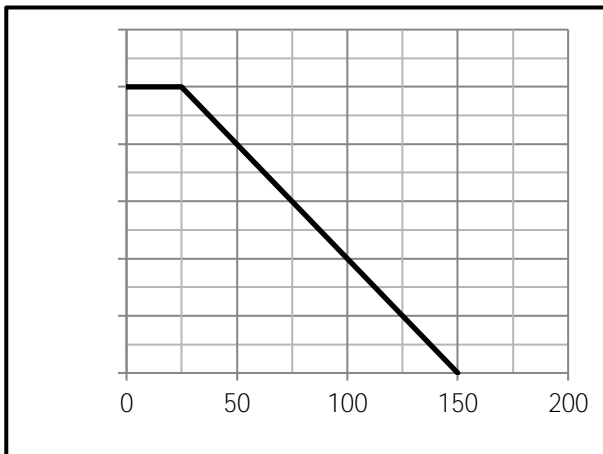


Fig.3 Typical output Characteristics

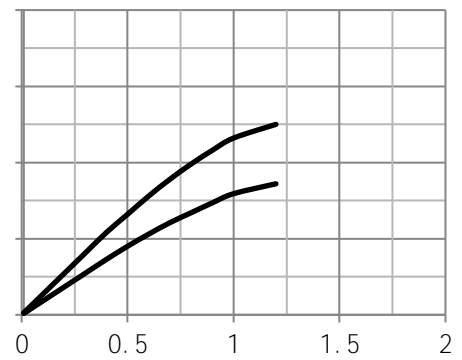


Fig.4 Threshold Voltage V.S Junction Temperature

Fig.5 Resistance V.S Drain Current

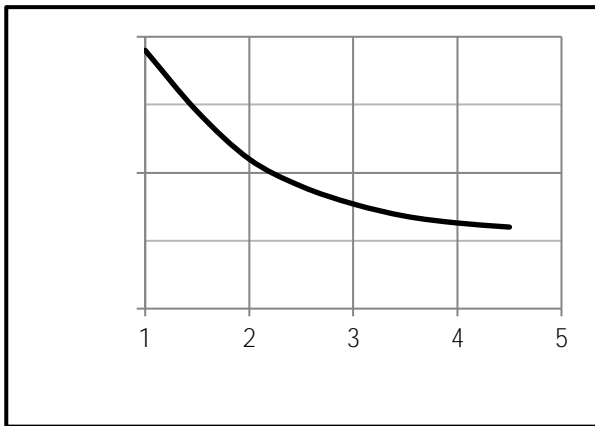


Fig.8 Switching Time Measurement Circuit

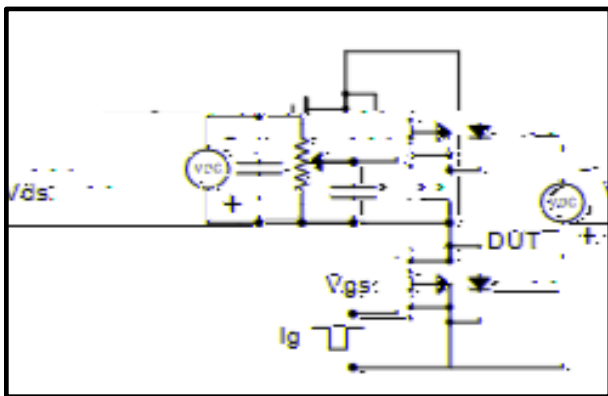


Fig.10 Switching Time Measurement Circuit

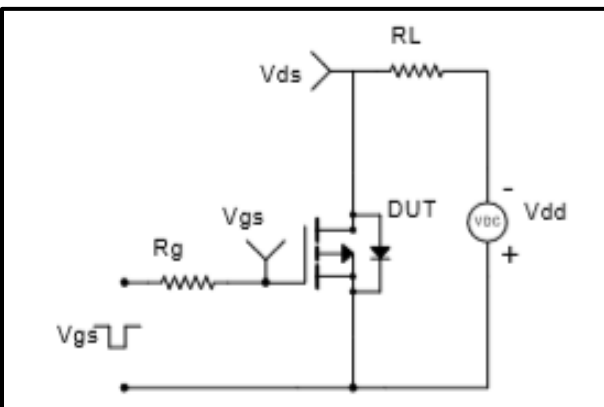


Fig.9 Gate Charge Waveform

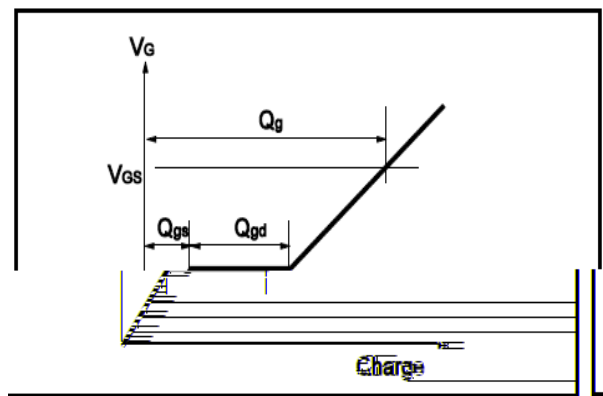
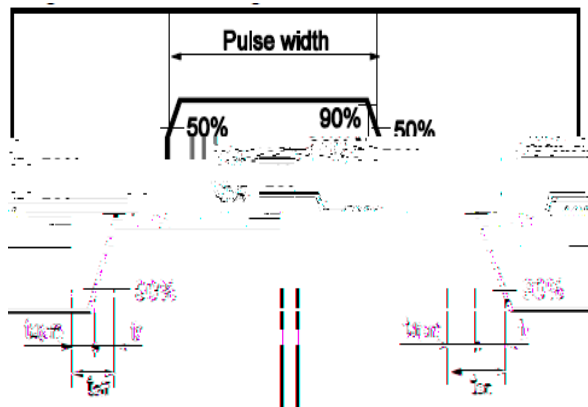


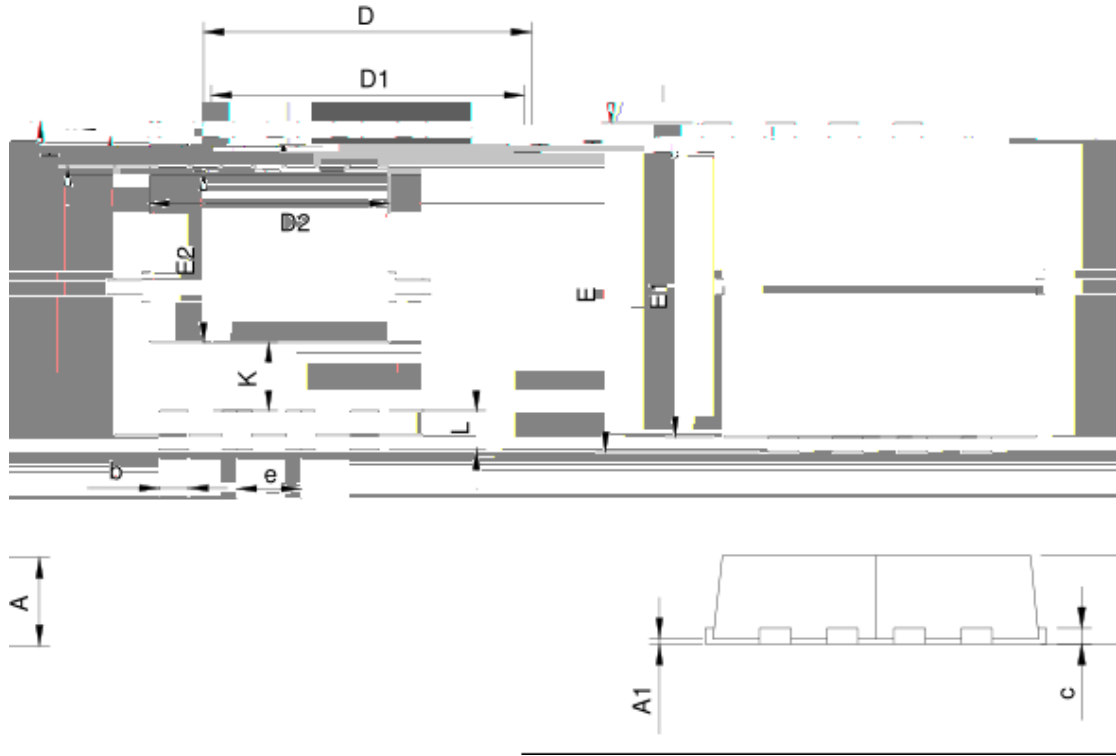
Fig.11 Gate Charge Waveform





sions(DFN3x3)

Unit mm



DFN3.3x3.3-8		RECOMMENDED LAND PATTERN			
		MILLIMETERS		MILS	
		MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039	
A1	0.00	0.05	0.000	0.002	
b	0.25	0.35			0.010
c	0.14	0.20			0.006
D	3.10	3.50			0.122
D1	3.05	3.25			0.120
D2	2.35	2.55	0.093	0.100	
E	3.10	3.50	0.122	0.138	
E1	2.90	3.10	0.114	0.122	
E2	2.35	2.55	0.093	0.100	
e	0.65 BSC	0.52	0.013	0.020	
H	0.32	0.52	0.013	0.020	
K	0.59	0.79	0.023	0.031	
L	0.25	0.35	0.010	0.022	